

PIMZ2; PUMZ2 NPN/PNP general-purpose double transistors Rev. 06 — 17 November 2009

Product data sheet

Product profile

1.1 General description

NPN/PNP general-purpose double transistors.

Table 1. **Product overview**

Type number	ype number Package		Configuration
	NXP	JEITA	
PIMZ2	SOT457	SC-74	NPN/PNP double transistors
PUMZ2	SOT363	SC-88	NPN/PNP double transistors

1.2 Features

- Simplified circuit design
- Reduced component count
- Reduced pick and place costs

1.3 Applications

■ General-purpose switching and amplification

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
I _C	collector current (DC)		-	-	150	mA



2. Pinning information

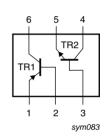
Table 3. Pinning

Pin	Description	Simplified outline	Symbol
PIMZ2 (S	SOT457)		
1	collector TR2		
2	emitter TR2	<u> </u>	6 5 4
3	collector TR1	0	
4	emitter TR1	<u> </u>	
5	base TR1		TR2
6	base TR2		1 2 3
			sym082
PHM72	(SOT363)		

PUMZ2 (SOT363)

1	emitter TR1
2	base TR1
3	base TR2
4	collector TR2
5	emitter TR2
6	collector TR1





3. Ordering information

Table 4. Ordering information

Type number	Package				
	Name	Description	Version		
PIMZ2	SC-74	plastic surface mounted package; 6 leads	SOT457		
PUMZ2	SC-88	plastic surface mounted package; 6 leads	SOT363		

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PIMZ2	M6
PUMZ2	GZ*

[1] * = -: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor; for the PNP transistor	with negative pola	rity		
V_{CBO}	collector-base voltage	open emitter	-	60	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	7	V
I _C	collector current (DC)		-	150	mA
I _{CM}	peak collector current		-	200	mA
I _{BM}	peak base current		-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	SOT457		<u>[1]</u> -	200	mW
	SOT363		<u>[1]</u> -	180	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
Per device	9				
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	SOT457		[1] -	300	mW
	SOT363		<u>[1]</u> _	300	mW

^[1] Device mounted on an FR4 printed-circuit board.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor					
$R_{th(j-a)}$	thermal resistance from junction to ambient	$T_{amb} \le 25 ^{\circ}C$				
	SOT457		[1] -	-	625	K/W
	SOT363		[1] -	-	694	K/W
Per devic	ce					
$R_{th(j-a)}$	thermal resistance from junction to ambient	$T_{amb} \le 25 ^{\circ}C$				
	SOT457		[1] -	-	417	K/W
	SOT363		<u>[1]</u> -	-	417	K/W

^[1] Device mounted on an FR4 printed-circuit board.

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7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	Per transistor; for the PNP transistor with negative polarity; unless otherwise specified					
I _{CBO}	collector-base cut-off current	$V_{CB} = 60 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
		V _{CB} = 60 V; I _E = 0 A; T _j = 150 °C	-	-	50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 7 \text{ V}; I_{C} = 0 \text{ A}$	-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 6 \text{ V}; I_{C} = 1 \text{ mA}$	120	250	560	
TR1 (PN	P)					
V _{CEsat}	collector-emitter saturation voltage	$I_C = -50 \text{ mA}; I_B = -5 \text{ mA}$	-	-	-500	mV
f _T	transition frequency	$I_E = -2 \text{ mA}; V_{CE} = -12 \text{ V}; f = 100 \text{ MHz}$	-	190	-	MHz
C _c	collector capacitance	$I_E = i_e = 0 \text{ A}; V_{CB} = -12 \text{ V}; f = 1 \text{ MHz}$	-	2.3	5	pF
TR2 (NP	N)					
V _{CEsat}	collector-emitter saturation voltage	$I_C = 50 \text{ mA}; I_B = 5 \text{ mA}$	-	-	250	mV
f _T	transition frequency	$I_E = 2 \text{ mA}; V_{CE} = 12 \text{ V}; f = 100 \text{ MHz}$	100	-	-	MHz
C _c	collector capacitance	$I_E = i_e = 0 \text{ A}; V_{CB} = 12 \text{ V}; f = 1 \text{ MHz}$	-	-	3	pF

8. Package outline

Plastic surface-mounted package (TSOP6); 6 leads

SOT457

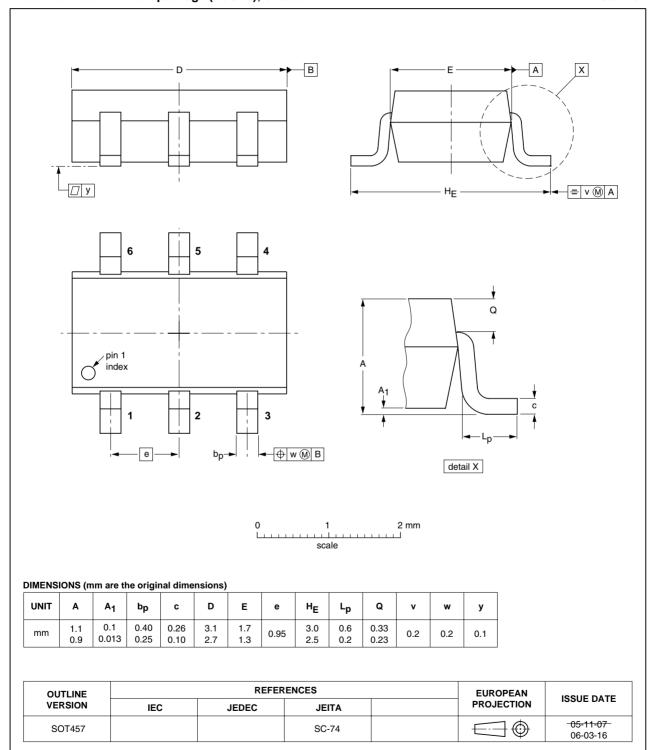


Fig 1. Package outline SOT457 (SC-74)

PIMZ2_PUMZ2_6

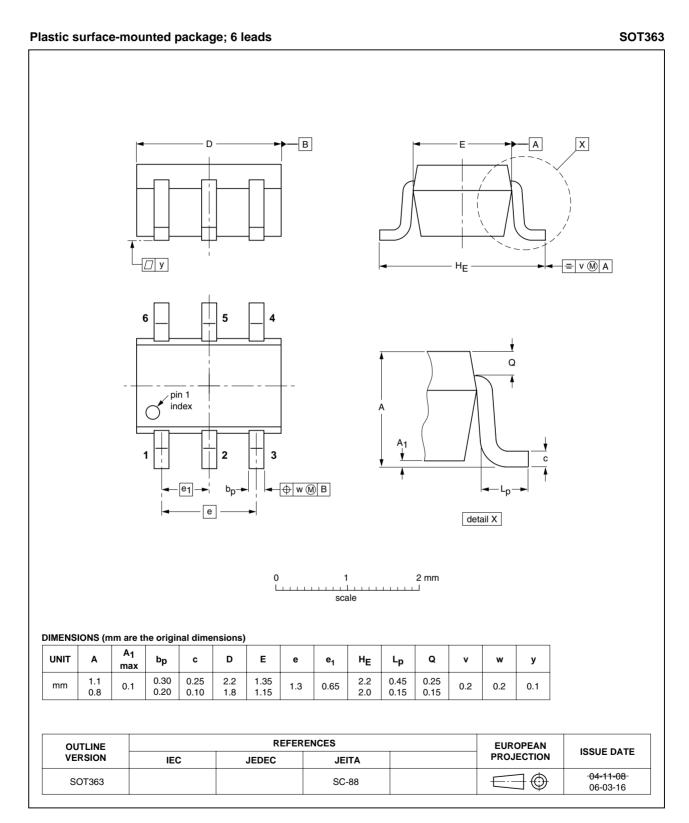


Fig 2. Package outline SOT363 (SC-88)

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Revision history

Table 9. **Revision history**

Product data sheet

Document ID	Release date	Data sheet status	Change notice	Supersedes
PIMZ2_PUMZ2_6	20091117	Product data sheet	-	PIMZ2_PUMZ2_5
Modifications:	 This data sheet was changed to reflect the new company name NXP Semiconduction including new legal definitions and disclaimers. No changes were made to the tectontent. Table 3 "Pinning": updated Figure 1 "Package outline SOT457 (SC-74)": updated Figure 2 "Package outline SOT363 (SC-88)": updated 			
PIMZ2_PUMZ2_5	20041124	Product data sheet	-	PIMZ2_PUMZ2_4
PIMZ2_PUMZ2_4	20031217	Product specification	-	PIMZ2_2
PIMZ2_2	20030714	Product specification	-	PIMZ2_1
PIMZ2_1	20030602	Objective specification	-	-

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10. Legal information

10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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